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Terms	Documents
L1 near2 ((titanium adj nitride) or (TiN))	2

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Search History**DATE: Tuesday, January 18, 2005** [Printable Copy](#) [Create Case](#)**Set Name** Query
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<u>L1</u>	857	<u>L1</u>

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Search Results - Record(s) 1 through 2 of 2 returned.

1. Document ID: US 6281052 B1

L2: Entry 1 of 2

File: USPT

Aug 28, 2001

US-PAT-NO: 6281052

DOCUMENT-IDENTIFIER: US 6281052 B1

TITLE: Method of manufacturing semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	RUMC	Drawn
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2. Document ID: US 4900257 A

L2: Entry 2 of 2

File: USPT

Feb 13, 1990

US-PAT-NO: 4900257

DOCUMENT-IDENTIFIER: US 4900257 A

TITLE: Method of making a polycide gate using a titanium nitride capping layer

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	RUMC	Drawn
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L2: Entry 1 of 2

File: USPT

Aug 28, 2001

DOCUMENT-IDENTIFIER: US 6281052 B1

TITLE: Method of manufacturing semiconductor device

Brief Summary Text (9):

In the titanium polycide gate, a titanium nitride (TiN) film barrier is formed between the titanium silicide (TiSi) film and the polysilicon (poly-Si) film usually by sputtering, so that impurity diffusion from the polysilicon film to the titanium silicide film is prevented, thereby preventing degradation in heat resistance during annealing.

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L2: Entry 2 of 2

File: USPT

Feb 13, 1990

DOCUMENT-IDENTIFIER: US 4900257 A

TITLE: Method of making a polycide gate using a titanium nitride capping layer[Previous Doc](#) [Next Doc](#) [Go to Doc#](#)